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Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 2

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| Application Number | 09/857,859 |
| Filing Date | 06/11/2001 |
| First Named Inventor | Dr. Bernd HEINEMANN |
| Group Art Unit | |
| Examiner Name | |
| Attorney Docket Number | 7040-30 |

U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

| Examiner Initials ² | Cite No. ¹ | Foreign Patent Document | | | Name of Patentee or Applicant of Cited Document | Date of Publication of Cited Document MM-DD-YYYY | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear | T ⁶ |
|--------------------------------|-----------------------|-------------------------|---------------------|--------------------------------------|---|---|---|----------------|
| | | Office ³ | Number ⁴ | Kind Code ⁵ (if known) | | | | |
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| Examiner Signature | T. NGUYEN |
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| Date Considered | 7/18/03 |
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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| Attorney Docket Number | 7040-30 |

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T. NGUYEN

7/11/03

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| Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i> | | | Complete if Known | | |
| | | | Application Number | 09/857,859 | |
| | | | Filing Date | 06/11/2001 | |
| | | | First Named Inventor | Dr. Bernd HEINEMANN | |
| | | | Group Art Unit | | |
| | | | Examiner Name | | |
| | | | Attorney Docket Number | 7040-30 | |
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| OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS | | | |
|--|-----------------------|---|----------------|
| Examiner Initials ² | Cite No. ¹ | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. | T ² |
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